

TENTATIVE

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

HN2C10FT

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

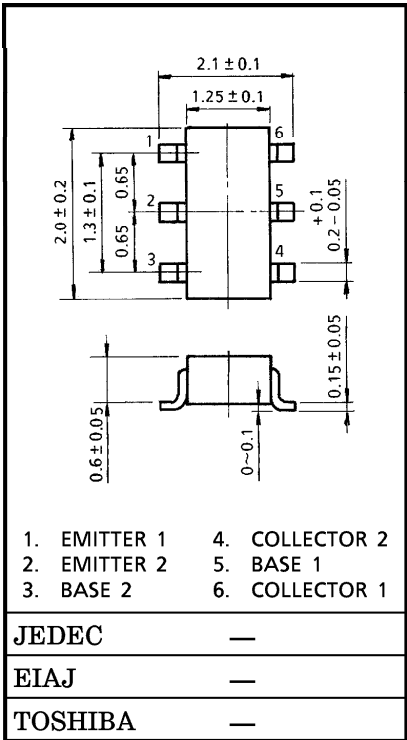
- TWO devices are built in to the super-thin and ultra super mini (6pins) package : TU6

MOUNTED DEVICES

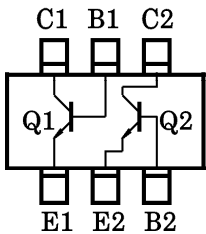
	Q1 / Q2
Three-pins (SSM) mold products are corresponded	2SC5086

MAXIMUM RATINGS (Ta = 25°C)

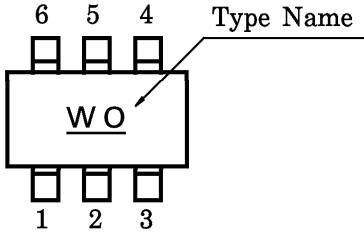
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	20	V
Collector-Emitter Voltage	VCEO	12	V
Emitter-Base Voltage	VEBO	3	V
Collector Current	IC	80	mA
Base Current	IB	40	mA
Collector Power Dissipation	PC	200	mW
Junction Temperature	Tj	125	°C
Storage Temperature Range	Tstg	-55~125	°C



PIN ASSIGNMENT (TOP VIEW)



MARKING



961001EAA1

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ELECTRICAL CHARACTERISTICS (Q1, Q2) (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 10V, I_E = 0$	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1V, I_C = 0$	—	—	1	μA
DC Current Gain	h_{FE}	$V_{CE} = 10V, I_C = 20mA$	80	—	240	—
Transition Frequency	f_T	$V_{CE} = 10V, I_C = 20mA$	5	7	—	GHz
Insertion Gain	$ S_{21e} ^2 (1)$	$V_{CE} = 10V, I_C = 20mA, f = 500MHz$	—	16.5	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 10V, I_C = 20mA, f = 1GHz$	8	11.5	—	
Noise Figure	NF (1)	$V_{CE} = 10V, I_C = 5mA, f = 500MHz$	—	1	—	dB
	NF (2)	$V_{CE} = 10V, I_C = 5mA, f = 1GHz$	—	1.1	2	
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$ (Note)	—	0.55	1.05	pF
Reverse Transfer Capacitance	C_{re}		—	0.6	1.1	

(Note) C_{re} is measured by 3 terminal method capacitance bridge.